

### General Description

The MDD4N25 uses advanced Magnachip's MOSFET Technology, which provides low on-state resistance, high switching performance and excellent quality.

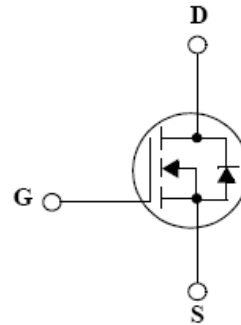
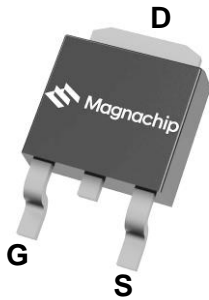
MDD4N25 is suitable device for SMPS, HID and general purpose applications.

### Features

- $V_{DS} = 250V$
- $I_D = 3.0A$
- $R_{DS(ON)} \leq 1.75\Omega$  @  $V_{GS} = 10V$

### Applications

- Power Supply
- PFC
- LED TV



### Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit	
Drain-Source Voltage	$V_{DSS}$	250	V	
Gate-Source Voltage	$V_{GSS}$	±30	V	
Continuous Drain Current	$I_D$	$T_C=25^\circ C$	3.0	A
		$T_C=100^\circ C$	1.9	A
Pulsed Drain Current <sup>(1)</sup>	$I_{DM}$	12	A	
Power Dissipation	$P_D$	$T_C=25^\circ C$	37	W
		Derivate above 25 °C	0.29	W/°C
Peak Diode Recovery $dv/dt$ <sup>(3)</sup>	$dv/dt$	5.5	V/ns	
Repetitive Pulse Avalanche Energy <sup>(4)</sup>	$E_{AR}$	3.7	mJ	
Avalanche current <sup>(1)</sup>	$I_{AR}$	3.0	A	
Single Pulse Avalanche Energy <sup>(4)</sup>	$E_{AS}$	52	mJ	
Junction and Storage Temperature Range	$T_J, T_{stg}$	-55~150	°C	

### Thermal Characteristics

Characteristics	Symbol	Rating	Unit
Thermal Resistance, Junction-to-Ambient <sup>(1)</sup>	$R_{\theta JA}$	110	°C/W
Thermal Resistance, Junction-to-Case <sup>(1)</sup>	$R_{\theta JC}$	3.4	

## Ordering Information

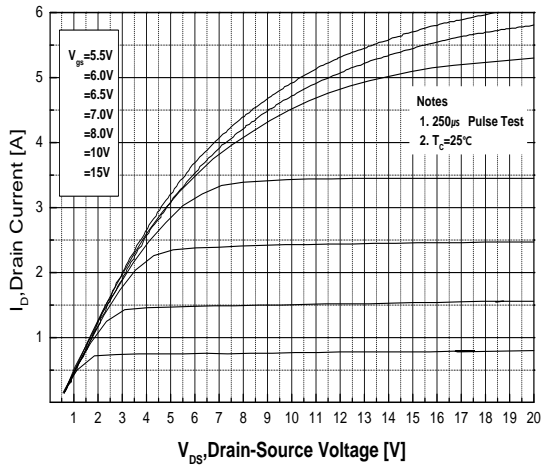
Part Number	Marking	Temp. Range	Package	Packing	RoHS Status
MDD4N25RH	MDD4N25	-55~150°C	TO-252(DPAK)	Reel and Tape	Halogen Free

## Electrical Characteristics (Ta =25°C)

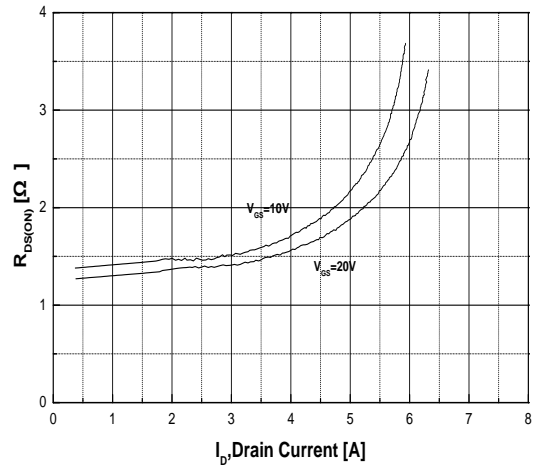
Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
<b>Static Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$I_D = 250\mu A, V_{GS} = 0V$	250	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	3.0	-	5.0	
Drain Cut-Off Current	$I_{DSS}$	$V_{DS} = 250V, V_{GS} = 0V$	-	-	1	$\mu A$
Gate Leakage Current	$I_{GSS}$	$V_{GS} = \pm 30V, V_{DS} = 0V$	-	-	100	nA
Drain-Source ON Resistance	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 1.5A$	-	1.38	1.75	$\Omega$
Forward Transconductance	$g_{fs}$	$V_{DS} = 30V, I_D = 1.5A$	-	1.7	-	S
<b>Dynamic Characteristics</b>						
Total Gate Charge	$Q_g$	$V_{DS} = 200V, I_D = 3.6A, V_{GS} = 10V$	-	4.2	-	nC
Gate-Source Charge	$Q_{gs}$		-	1.35	-	
Gate-Drain Charge	$Q_{gd}$		-	1.95	-	
Input Capacitance	$C_{iss}$	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz$	-	146	-	pF
Reverse Transfer Capacitance	$C_{rss}$		-	3	-	
Output Capacitance	$C_{oss}$		-	32	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{GS} = 5V, V_{DS} = 125V, I_D = 3.6A, R_G = 25\Omega$	-	8	-	ns
Rise Time	$t_r$		-	21	-	
Turn-Off Delay Time	$t_{d(off)}$		-	5	-	
Fall Time	$t_f$		-	16	-	
<b>Drain-Source Body Diode Characteristics</b>						
Maximum Continuous Drain to Source Diode Forward Current	$I_S$		-	-	3.0	A
Source-Drain Diode Forward Voltage	$V_{SD}$	$I_S = 3.0A, V_{GS} = 0V$	-	-	1.5	V
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F = 3.6A, di/dt = 100A/\mu s^{(3)}$	-	110	-	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$		-	0.34	-	$\mu C$

Note :

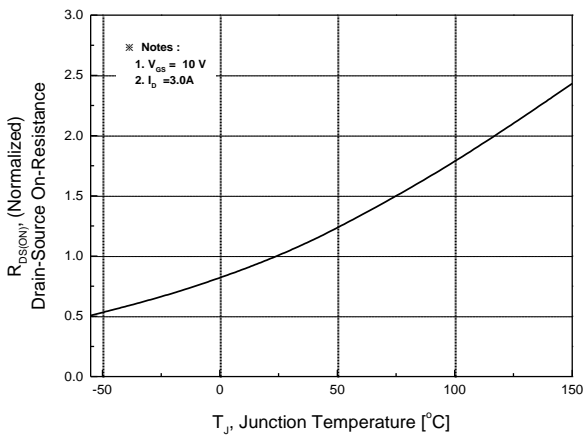
1. Pulse width is based on  $R_{\theta JC}$  &  $R_{\theta JA}$  and the maximum allowed junction temperature of 150°C.
2. Pulse test: pulse width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$ , pulse width limited by junction temperature  $T_{J(MAX)} = 150^\circ C$ .
3.  $I_{SD} \leq 3.6A$ ,  $di/dt \leq 300A/\mu s$ ,  $V_{DD} \leq BV_{DSS}$ ,  $R_G = 25\Omega$ , Starting  $T_J = 25^\circ C$
4.  $L = 9.3mH$ ,  $I_{AS} = 3.0A$ ,  $V_{DD} = 50V$ ,  $R_G = 25\Omega$ , Starting  $T_J = 25^\circ C$



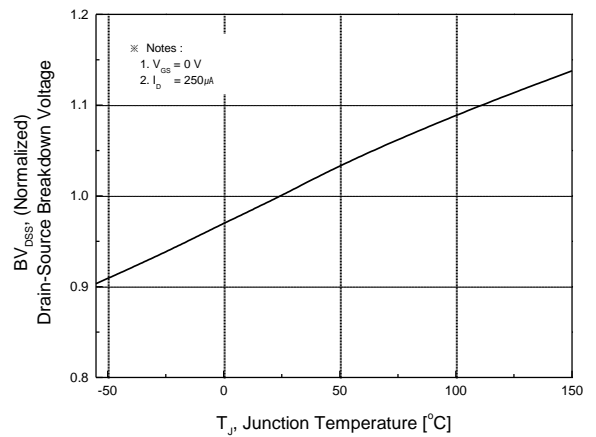
**Fig.1 On-Region Characteristics**



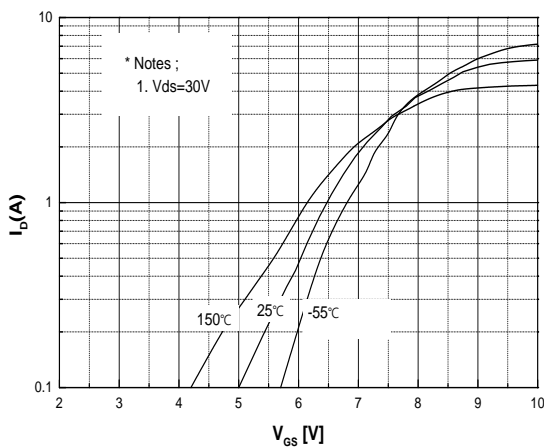
**Fig.2 On-Resistance Variation with Drain Current and Gate Voltage**



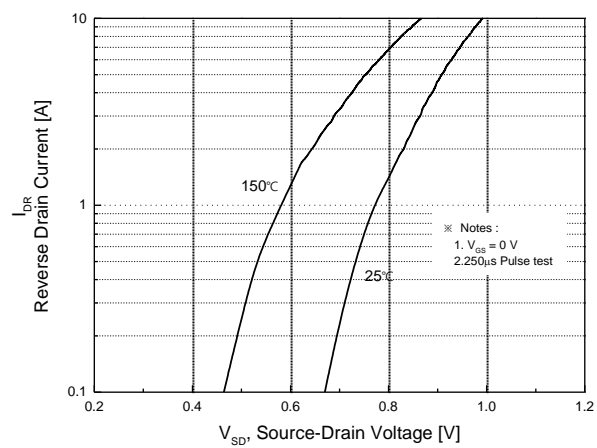
**Fig.3 On-Resistance Variation with Temperature**



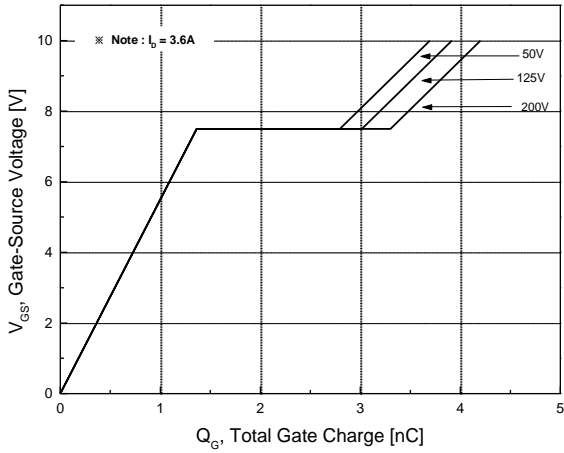
**Fig.4 Breakdown Voltage Variation vs. Temperature**



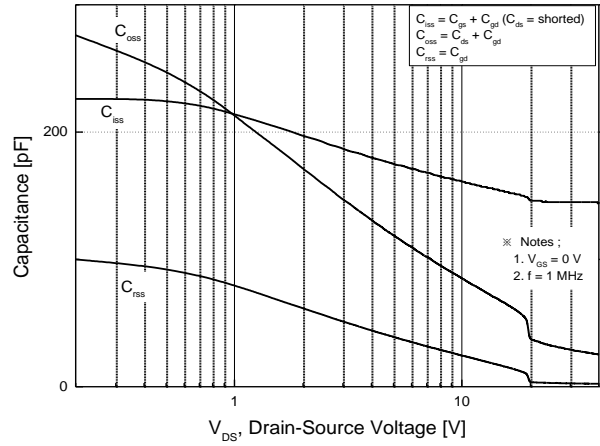
**Fig.5 Transfer Characteristics**



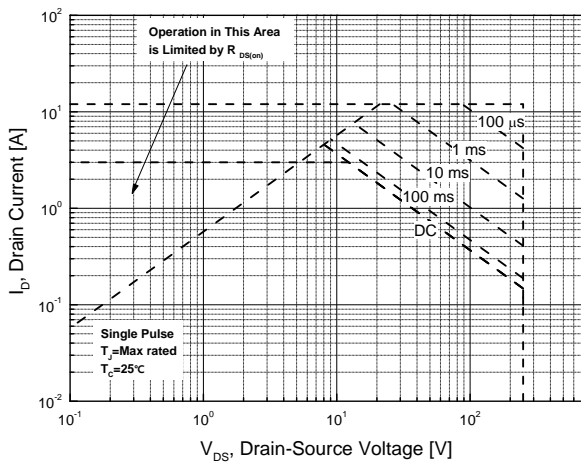
**Fig.6 Body Diode Forward Voltage Variation with Source Current and Temperature**



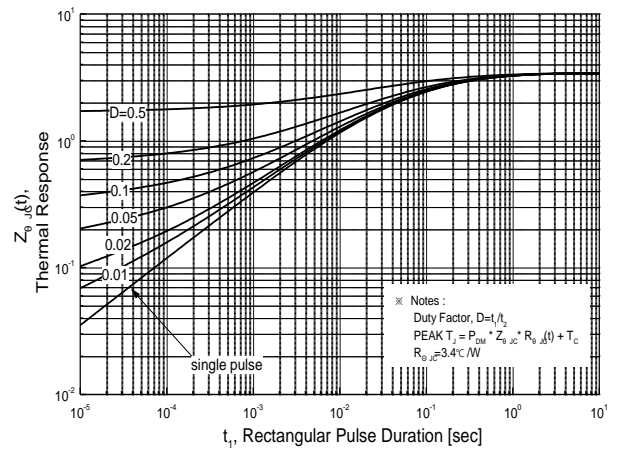
**Fig.7 Gate Charge Characteristics**



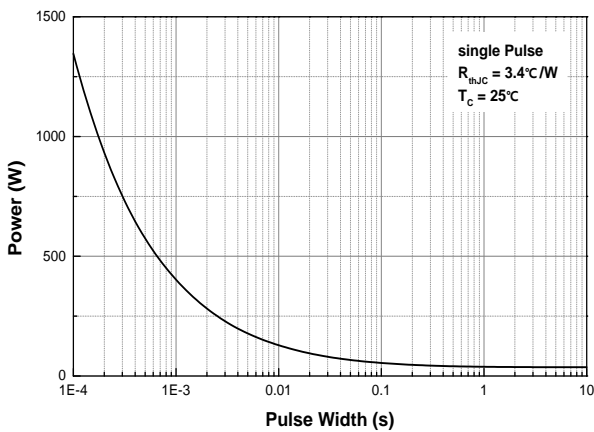
**Fig.8 Capacitance Characteristics**



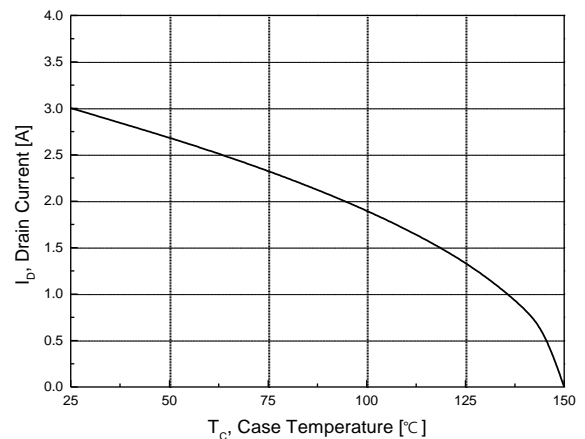
**Fig.9 Maximum Safe Operating Area**



**Fig.10 Transient Thermal Response Curve**



**Fig.11 Single Pulse Maximum Power Dissipation**

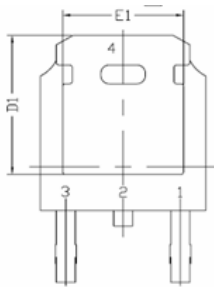
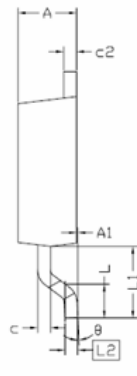
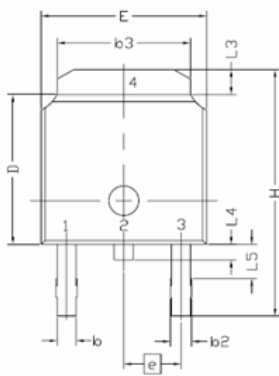


**Fig.12 Maximum Drain Current vs. Case Temperature**

## Physical Dimension

### TO-252 (DPAK)


Dimensions are in millimeters, unless otherwise specified



Symbol	Min.	Nom.	Max.
E	6,35	-	6,73
L	1,40	1,52	1,78
L1	2,74 REF		
L2	0,508 BCS		
L3	0,89	-	1,27
L4	-	-	1,02
L5	1,14	-	1,52
D	5,97	6,10	6,22
H	9,40	-	10,41
b	0,64	-	0,89
b2	0,76	-	1,14
b3	4,95	-	5,46
e	2,286 BSC		
A	2,18	-	2,39
A1	-	-	0,13
c	0,46	-	0,61
c2	0,46	-	0,89
D1	5,21	-	-
E1	4,32	-	-
⌀	0,00	-	10,00

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